

DATA SHEET

BFS520

NPN 9 GHz wideband transistor

Product specification

September 1995



NPN 9 GHz wideband transistor

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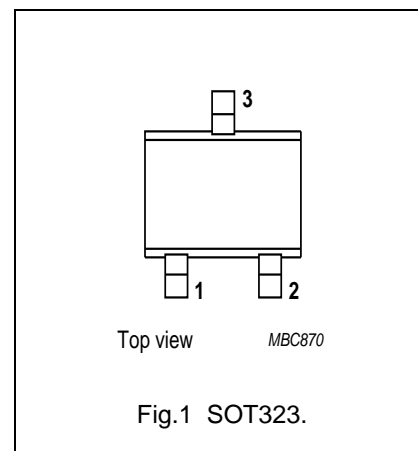
FEATURES

- High power gain
- Low noise figure
- High transition frequency
- Gold metallization ensures excellent reliability
- SOT323 envelope.

It is intended for wideband applications such as satellite TV tuners, cellular phones, cordless phones, pagers etc., with signal frequencies up to 2 GHz.

PINNING

PIN	DESCRIPTION
Code: N2	
1	base
2	emitter
3	collector



DESCRIPTION

NPN transistor in a plastic SOT323 envelope.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	20	V
V_{CES}	collector-emitter voltage	$R_{BE} = 0$	–	–	15	V
I_C	DC collector current		–	–	70	mA
P_{tot}	total power dissipation	up to $T_s = 118\text{ °C}$; note 1	–	–	300	mW
h_{FE}	DC current gain	$I_C = 20\text{ mA}$; $V_{CE} = 6\text{ V}$; $T_j = 25\text{ °C}$	60	120	250	
f_T	transition frequency	$I_C = 20\text{ mA}$; $V_{CE} = 6\text{ V}$; $f = 1\text{ GHz}$; $T_{amb} = 25\text{ °C}$	–	9	–	GHz
G_{UM}	maximum unilateral power gain	$I_C = 20\text{ mA}$; $V_{CE} = 6\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	15	–	dB
F	noise figure	$I_C = 5\text{ mA}$; $V_{CE} = 6\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	1.1	1.6	dB

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	20	V
V_{CES}	collector-emitter voltage	$R_{BE} = 0$	–	15	V
V_{EBO}	emitter-base voltage	open collector	–	2.5	V
I_C	DC collector current		–	70	mA
P_{tot}	total power dissipation	up to $T_s = 118\text{ °C}$; note 1	–	300	mW
T_{stg}	storage temperature		–65	150	°C
T_j	junction temperature		–	175	°C

Note

1. T_s is the temperature at the soldering point of the collector tab.

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THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	THERMAL RESISTANCE
$R_{th\ j-s}$	thermal resistance from junction to soldering point	up to $T_s = 118\text{ °C}$; note 1	190 K/W

Note

- T_s is the temperature at the soldering point of the collector tab.

CHARACTERISTICS

$T_j = 25\text{ °C}$, unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CE} = 6\text{ V}$	–	–	50	nA
h_{FE}	DC current gain	$I_C = 20\text{ mA}$; $V_{CE} = 6\text{ V}$	60	120	250	
C_e	emitter capacitance	$I_C = i_c = 0$; $V_{EB} = 0.5\text{ V}$; $f = 1\text{ MHz}$	–	1	–	pF
C_c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 6\text{ V}$; $f = 1\text{ MHz}$	–	0.5	–	pF
C_{re}	feedback capacitance	$I_C = 0$; $V_{CB} = 6\text{ V}$; $f = 1\text{ MHz}$	–	0.4	–	pF
f_T	transition frequency	$I_C = 20\text{ mA}$; $V_{CE} = 6\text{ V}$; $f = 1\text{ GHz}$; $T_{amb} = 25\text{ °C}$	–	9	–	GHz
G_{UM}	maximum unilateral power gain (note 1)	$I_C = 20\text{ mA}$; $V_{CE} = 6\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	15	–	dB
		$I_C = 20\text{ mA}$; $V_{CE} = 6\text{ V}$; $f = 2\text{ GHz}$; $T_{amb} = 25\text{ °C}$	–	9	–	dB
$ S_{21} ^2$	insertion power gain	$I_C = 20\text{ mA}$; $V_{CE} = 6\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$	13	14	–	dB
F	noise figure	$\Gamma_s = \Gamma_{opt}$; $I_C = 5\text{ mA}$; $V_{CE} = 6\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	1.1	1.6	dB
		$\Gamma_s = \Gamma_{opt}$; $I_C = 20\text{ mA}$; $V_{CE} = 6\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	1.6	2.1	dB
		$\Gamma_s = \Gamma_{opt}$; $I_C = 5\text{ mA}$; $V_{CE} = 6\text{ V}$; $f = 2\text{ GHz}$; $T_{amb} = 25\text{ °C}$	–	1.9	–	dB
P_{L1}	output power at 1 dB gain compression	$I_C = 20\text{ mA}$; $V_{CE} = 6\text{ V}$; $R_L = 50\text{ }\Omega$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	17	–	dBm
ITO	third order intercept point	note 2	–	26	–	dBm

Notes

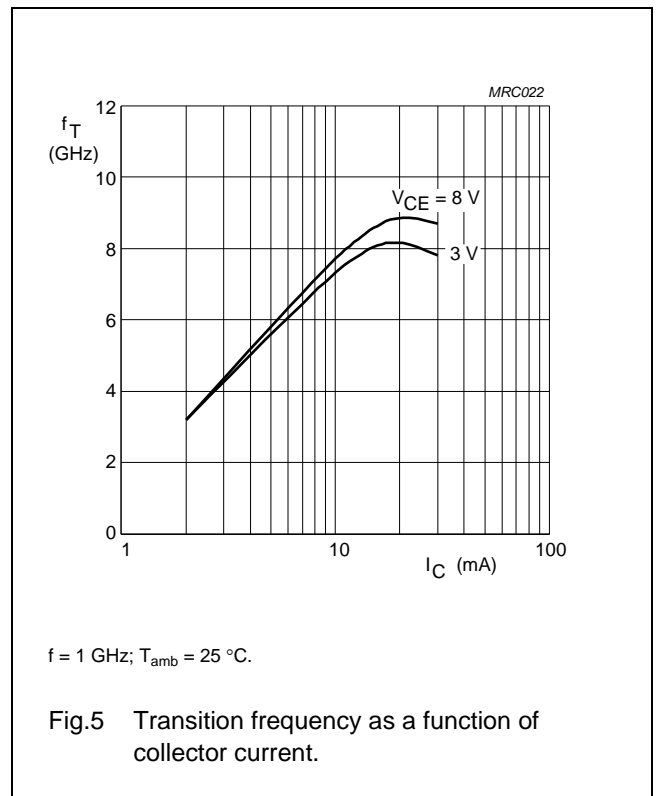
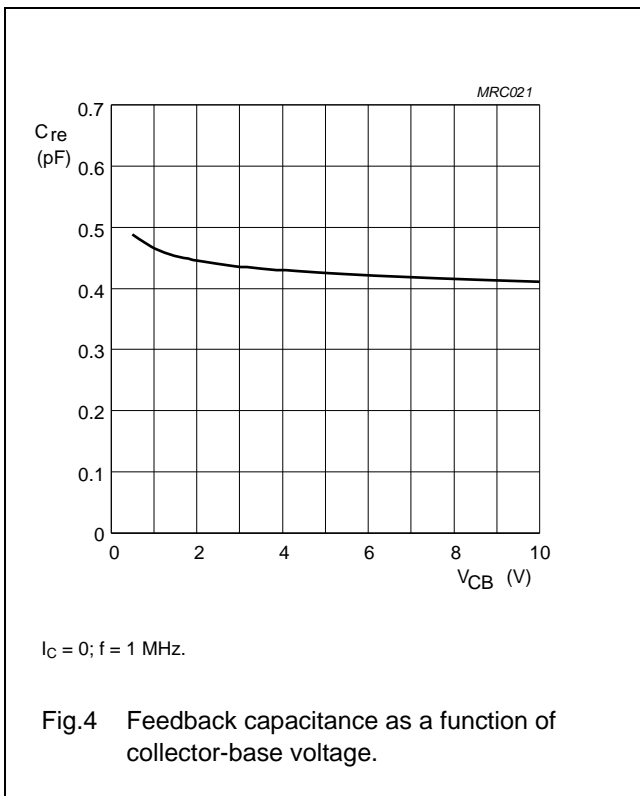
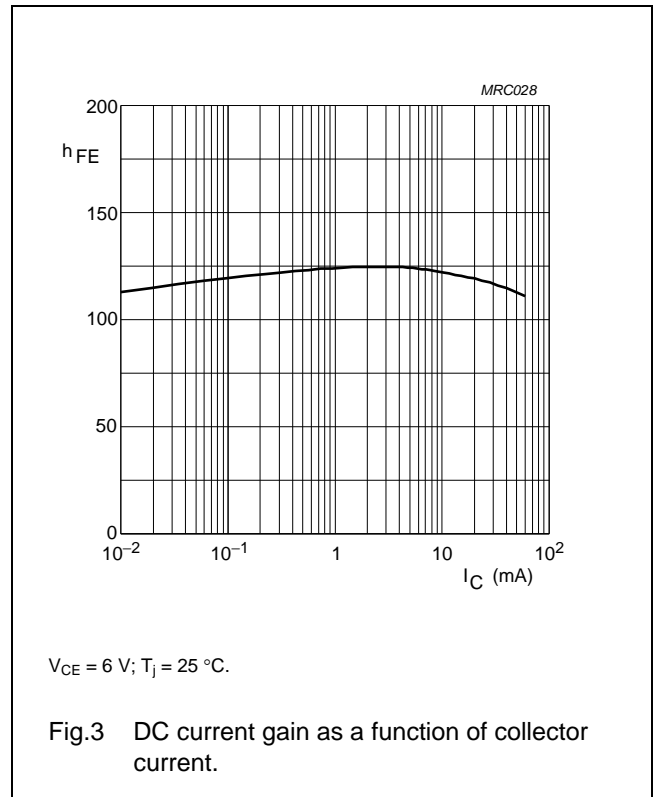
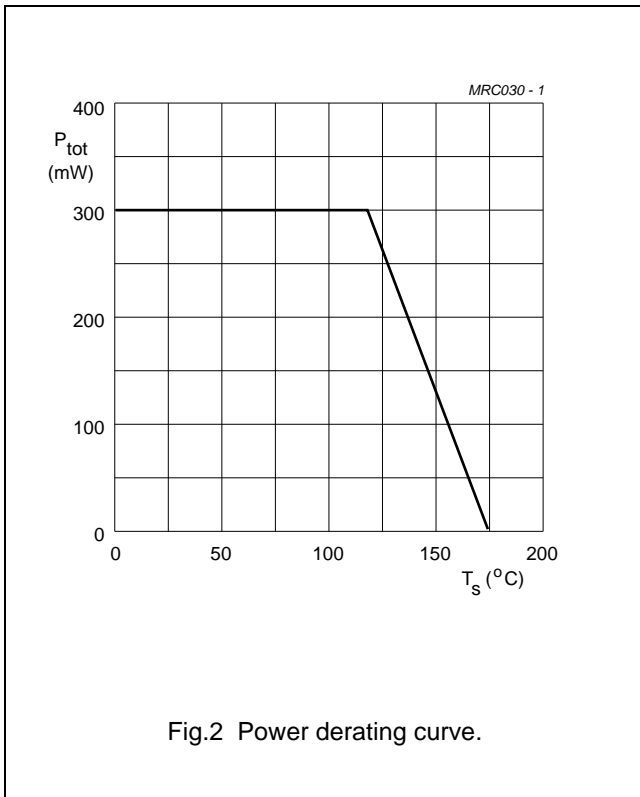
- G_{UM} is the maximum unilateral power gain, assuming S_{12} is zero and

$$G_{UM} = 10 \log \frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)} \text{ dB.}$$

- $I_C = 20\text{ mA}$; $V_{CE} = 6\text{ V}$; $R_L = 50\text{ }\Omega$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ °C}$;
 $f_p = 900\text{ MHz}$; $f_q = 902\text{ MHz}$; measured at $f_{(2p-q)} = 898\text{ MHz}$ and at $f_{(2q-p)} = 904\text{ MHz}$.

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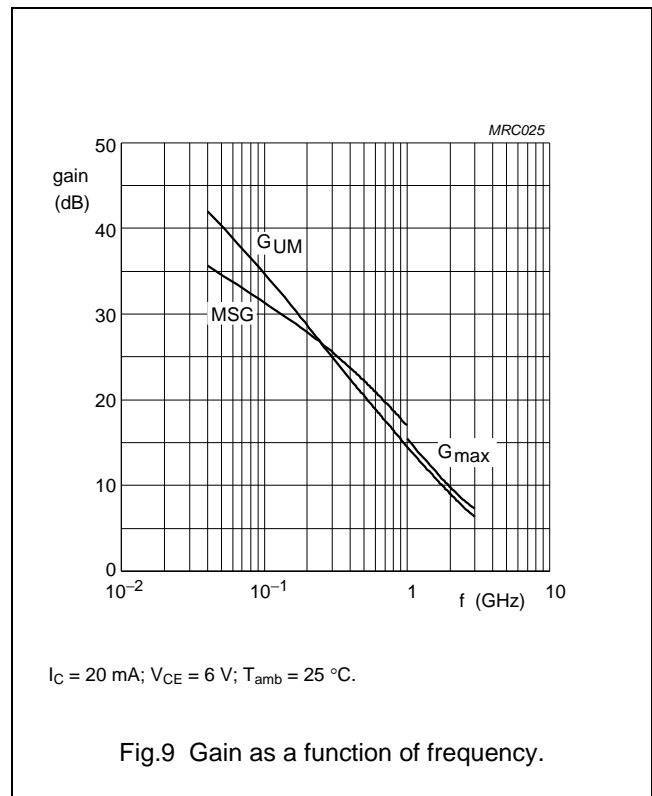
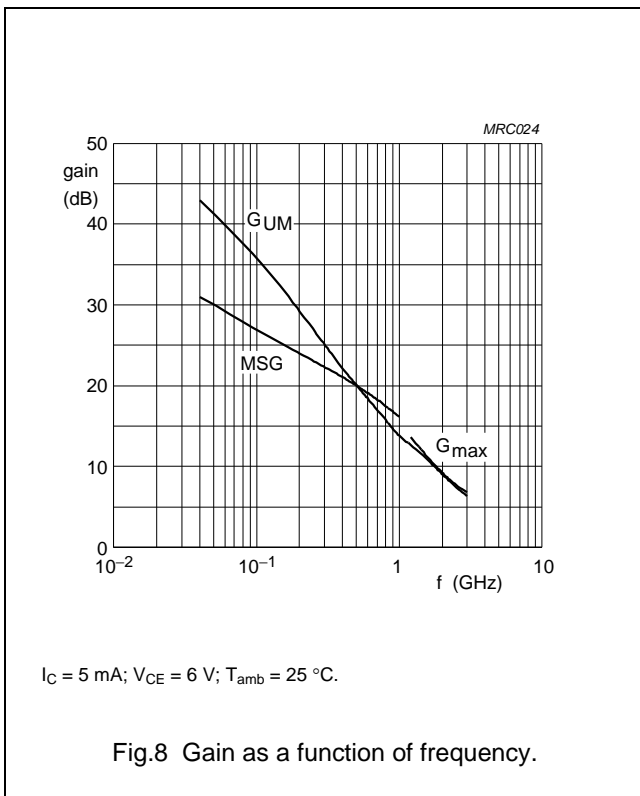
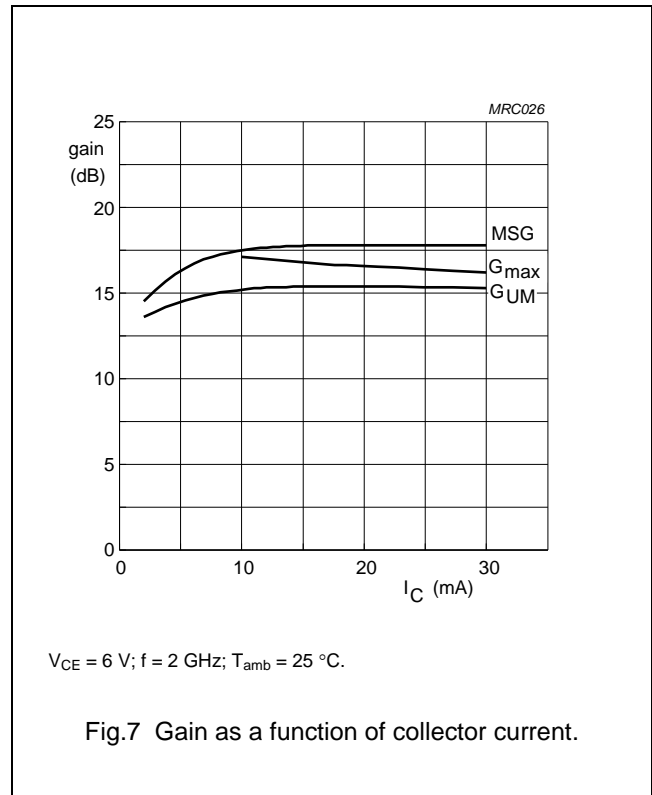
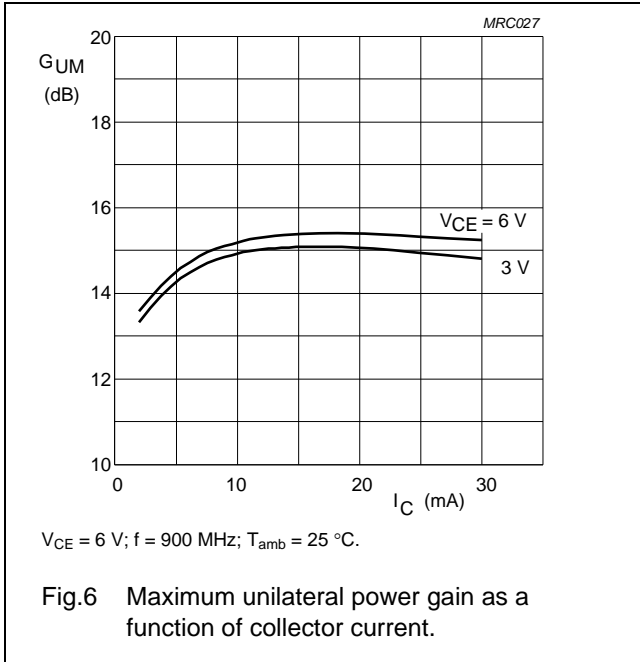
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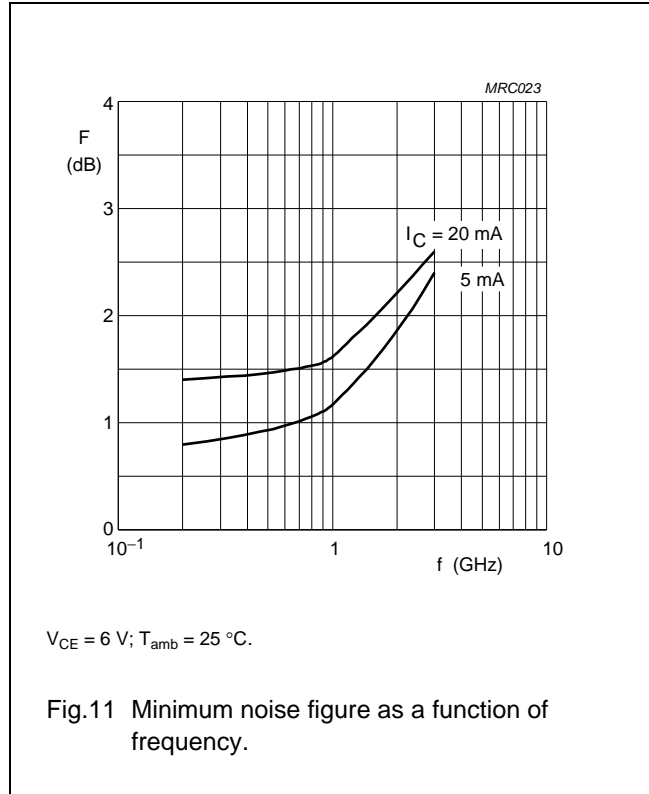
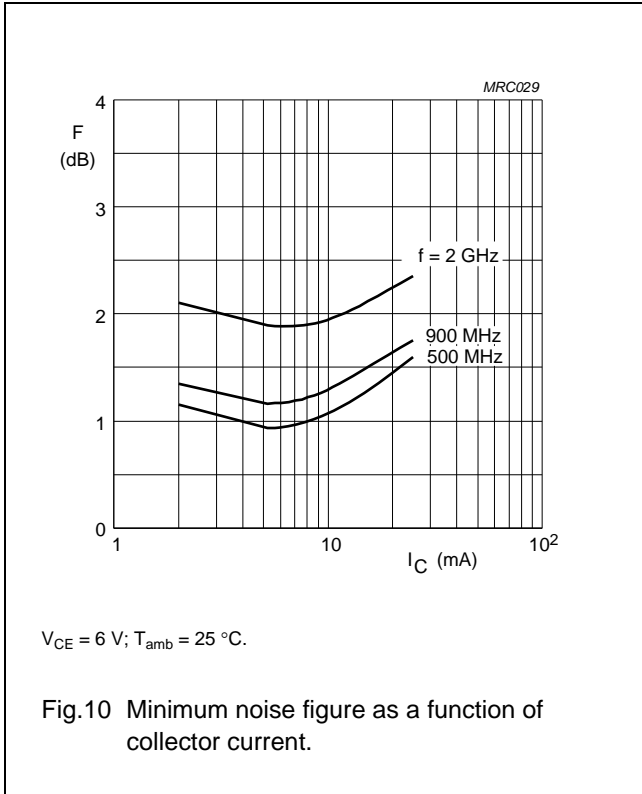
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In Figs 6 to 9, G_{UM} = maximum unilateral power gain; MSG = maximum stable gain; G_{max} = maximum available gain.



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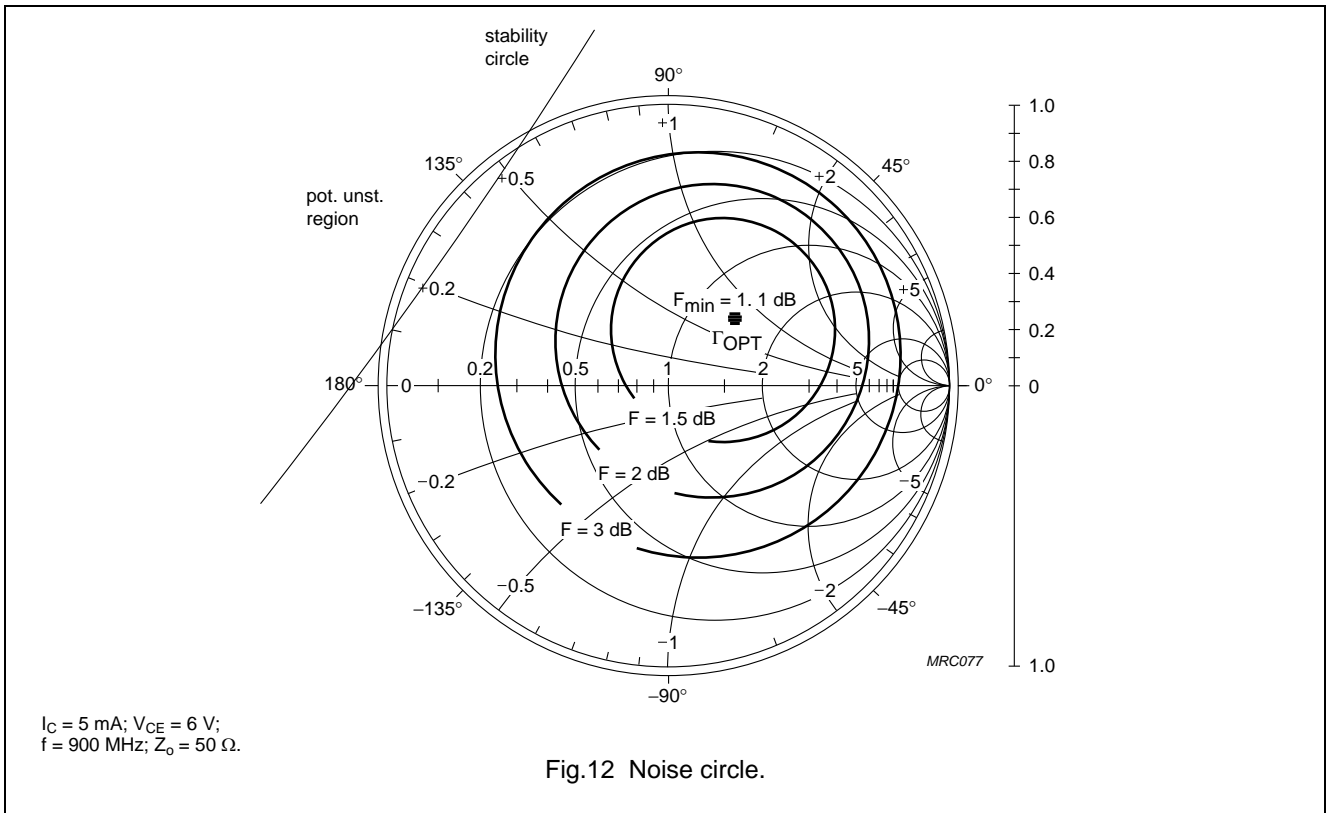


Fig.12 Noise circle.

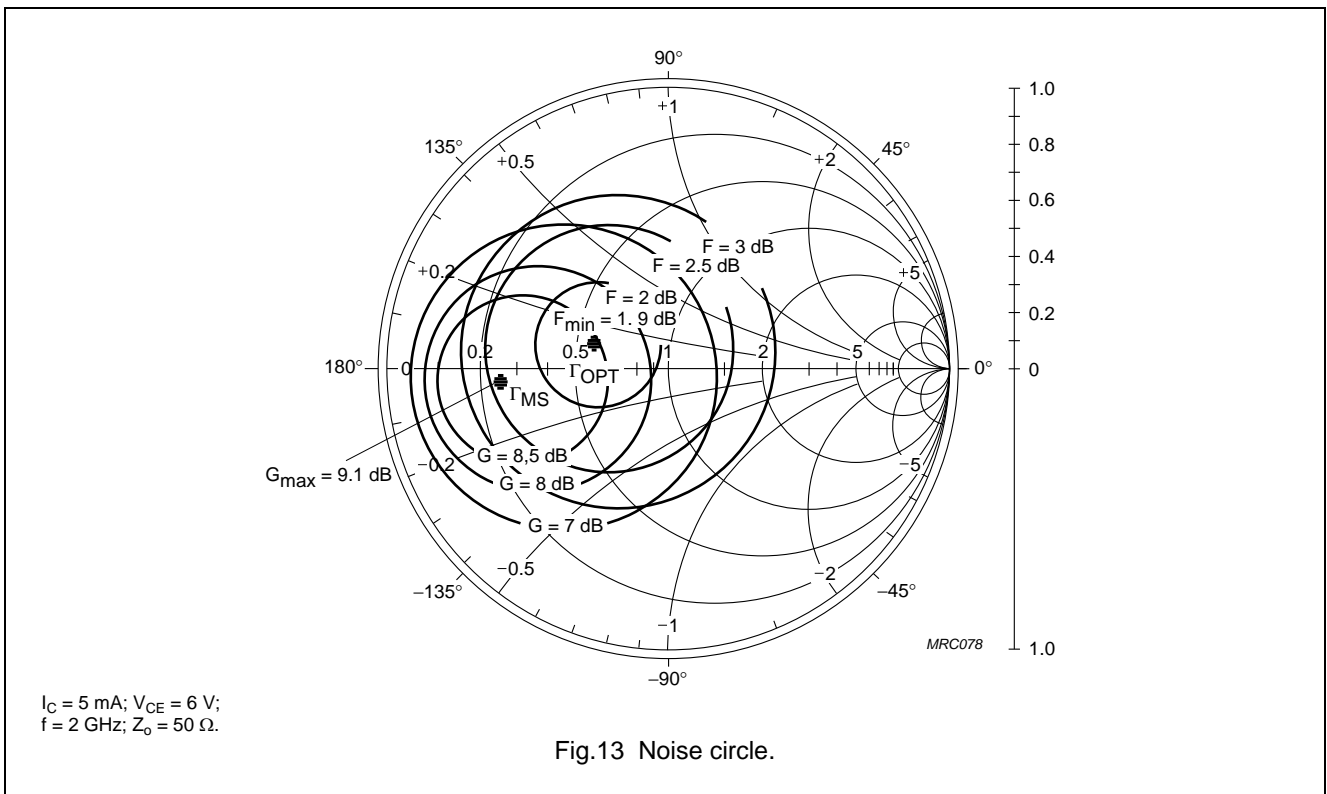
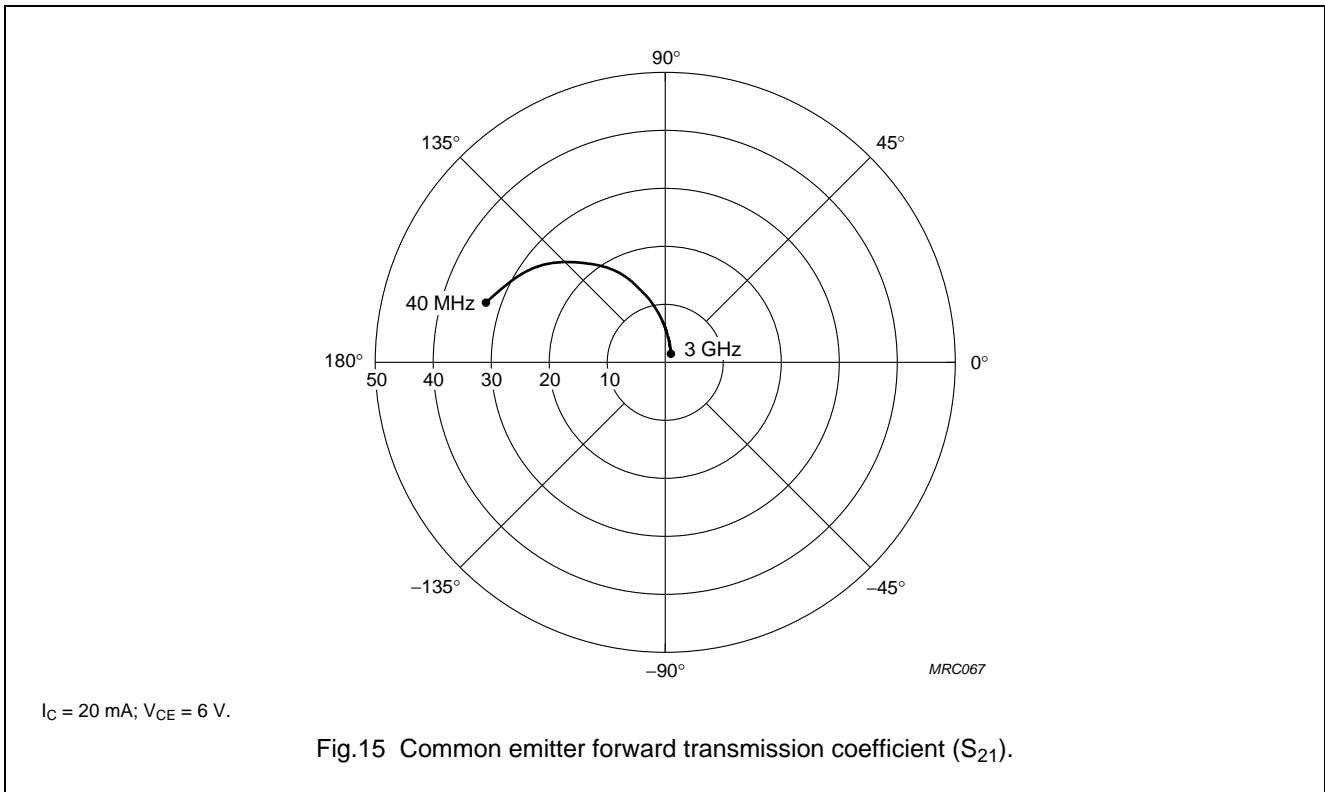
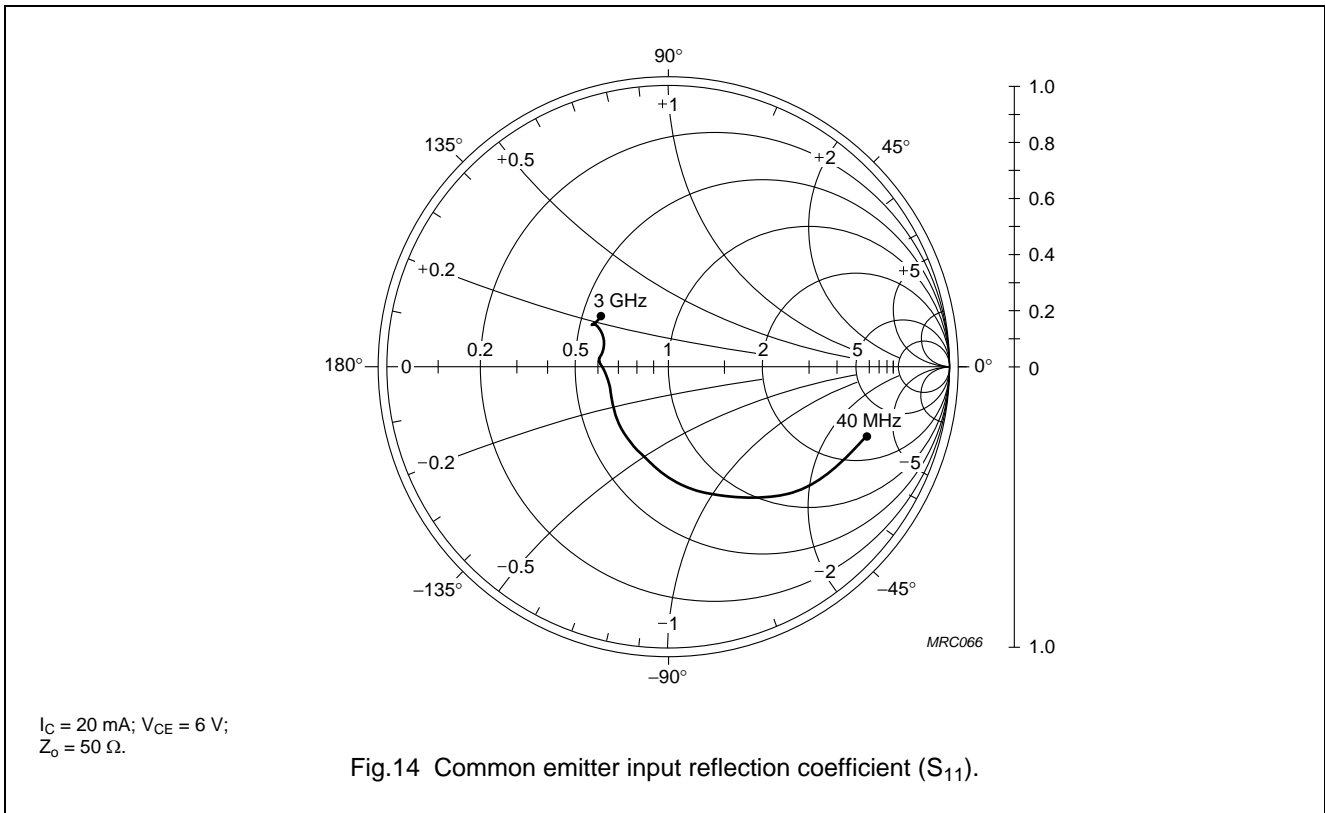


Fig.13 Noise circle.

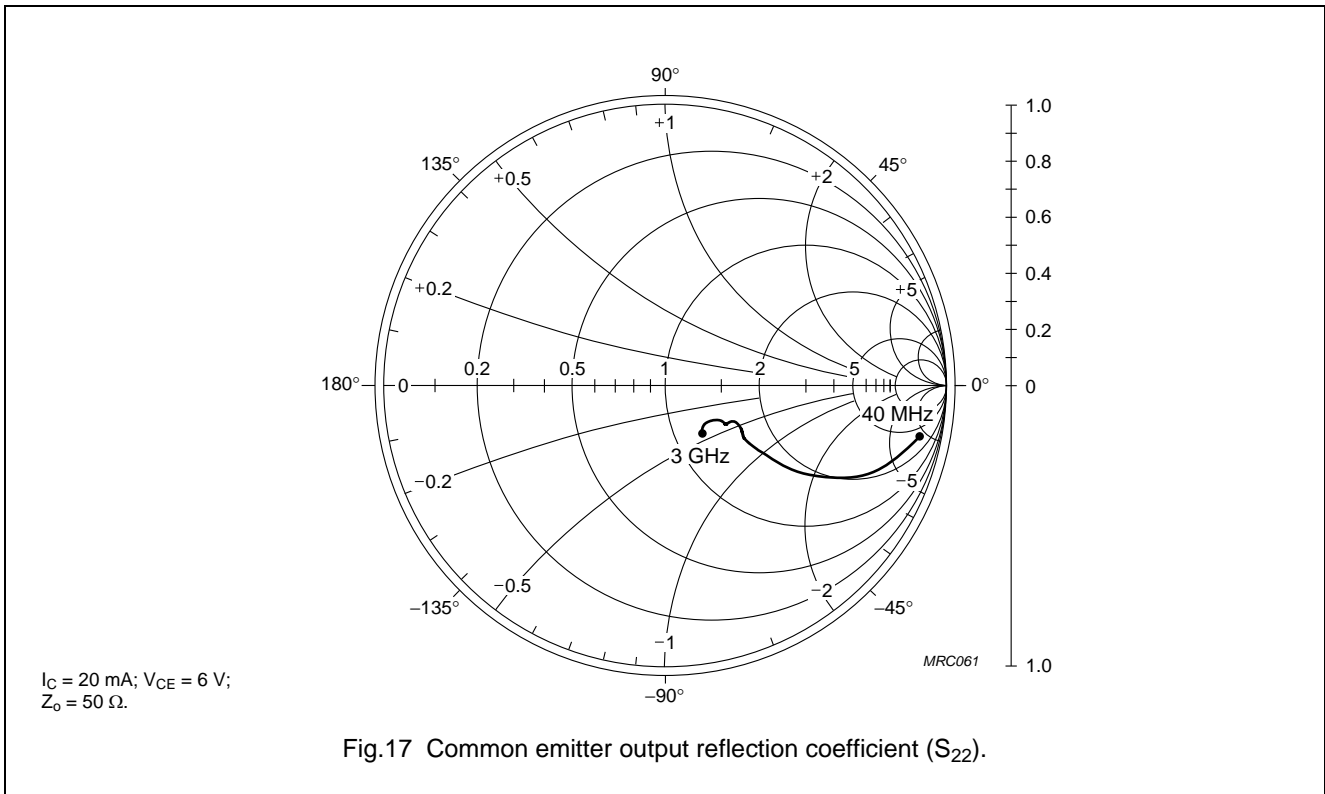
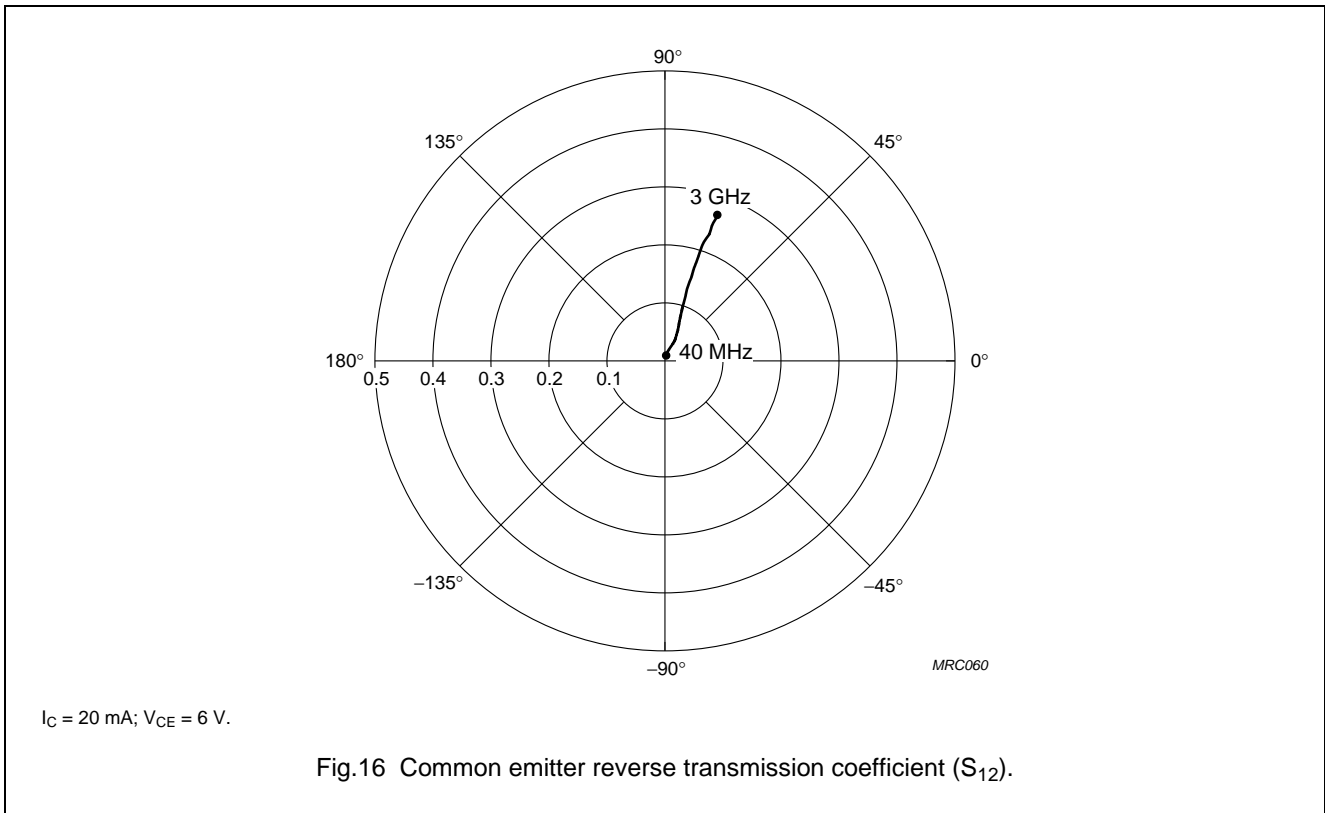
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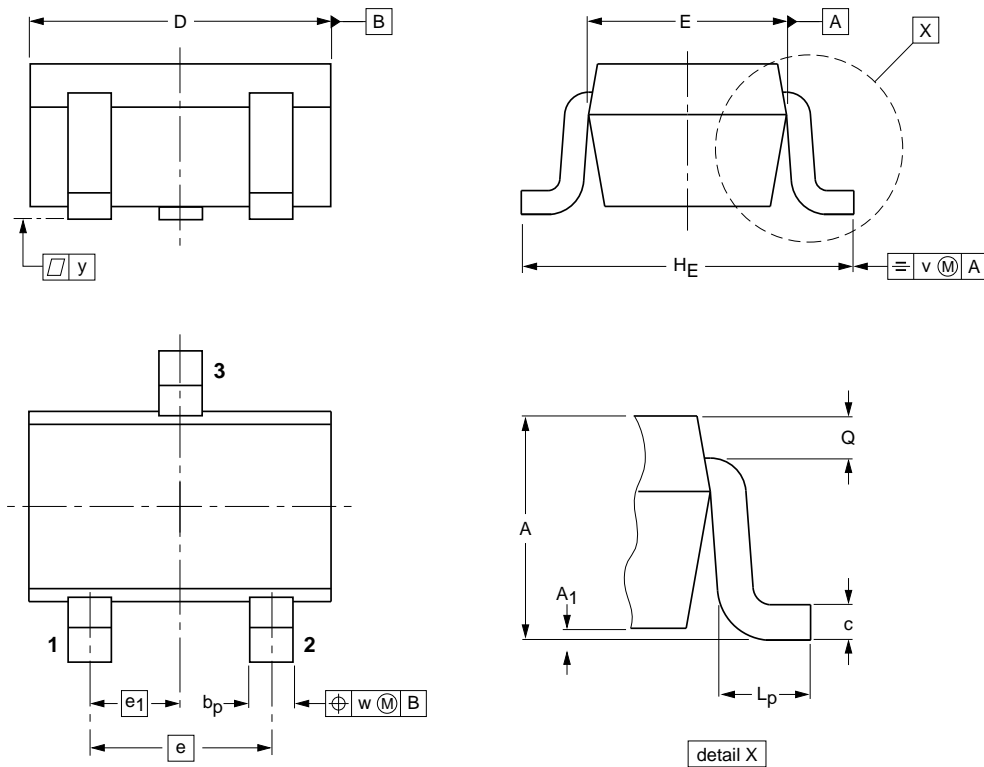
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PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT323			SC-70			04-11-04 06-03-16

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
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